

# PCM

Phase Change Memory







# Theory of Operation

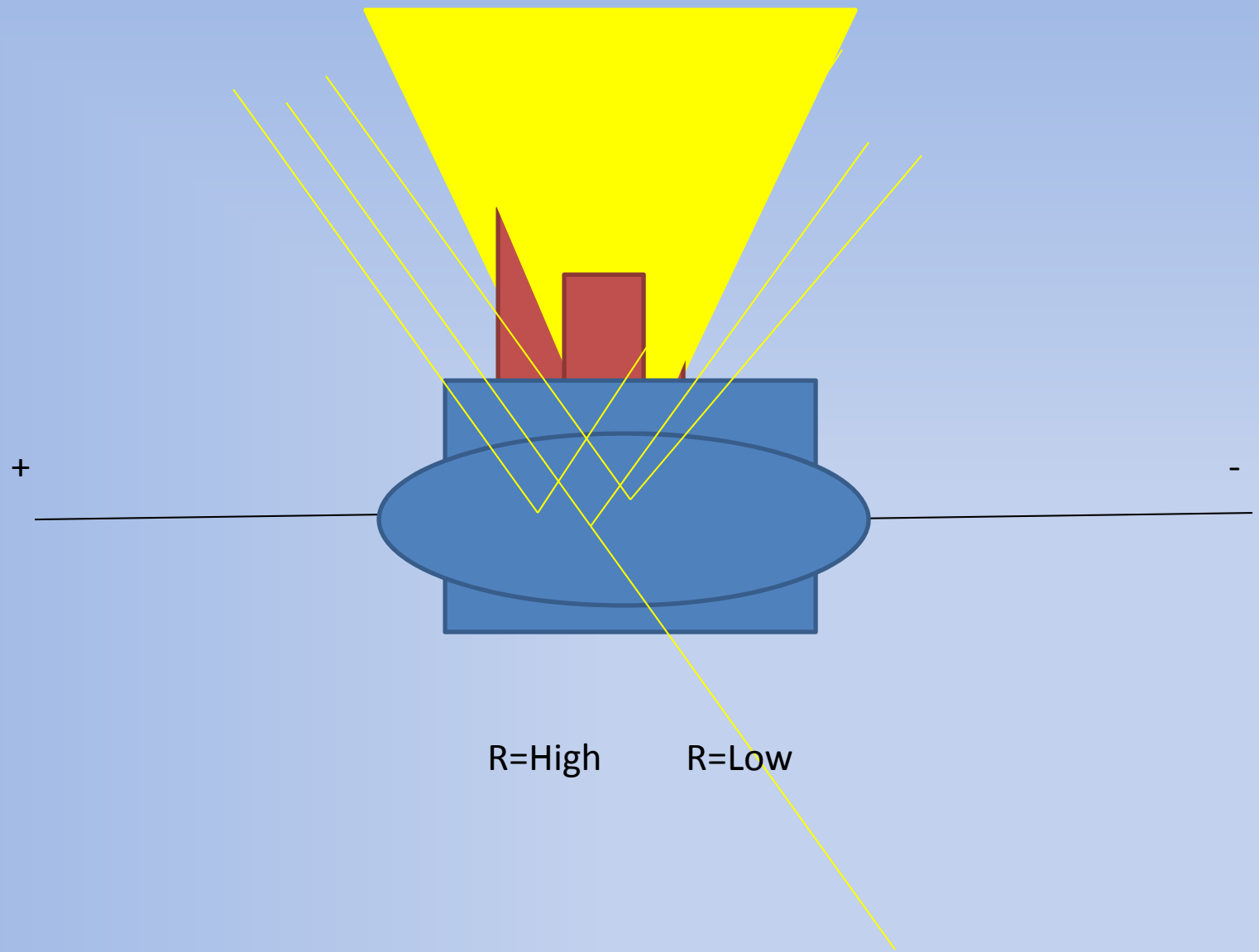
- Uses states of materials to represent bits instead of elections
  - Amorphous = “0”
  - Crystalline = “1”
- Other traits of the materials change with the states such as :
  - Resistivity
  - Reflectivity

# Type of Material

- Chalcogenide glass
- $\text{Ge}_2\text{Sb}_2\text{Te}_5$  (GST)
  - $\text{AgLnSbTe}$ ,  $\text{InSe}$ ,  $\text{SbSe}$ ,  $\text{InSbSe}$

				<b>He</b> Helium 4.003
6 <b>C</b> Carbon 12.0107	7 <b>N</b> Nitrogen 14.0067	8 <b>O</b> Oxygen 15.9994	9 <b>F</b> Fluorine 18.9984032	10 <b>Ne</b> Neon 20.1797
14 <b>Si</b> Silicon 28.0855	15 <b>P</b> Phosphorus 30.973761	16 <b>S</b> Sulfur 32.066	17 <b>Cl</b> Chlorine 35.4527	18 <b>Ar</b> Argon 39.948
32 <b>Ge</b> Germanium 72.61	33 <b>As</b> Arsenic 74.92160	34 <b>Se</b> Selenium 78.96	35 <b>Br</b> Bromine 79.904	36 <b>Kr</b> Krypton 83.80
50 <b>Sn</b> Tin 118.710	51 <b>Sb</b> Antimony 121.760	52 <b>Te</b> Tellurium 127.60	53 <b>I</b> Iodine 126.90447	54 <b>Xe</b> Xenon 131.29
82 <b>Pb</b> Lead 207.2	83 <b>Bi</b> Bismuth 208.9803	84 <b>Po</b> Polonium (209)	85 <b>At</b> Astatine (210)	86 <b>Rn</b> Radon (222)

Structure	Sample	Properties
Amorphous		<ul style="list-style-type: none"> <li>• Short-range atomic Order</li> <li>• High reflectivity</li> <li>• High resistivity</li> </ul>
		
Polycrystalline		<ul style="list-style-type: none"> <li>• Long-range atomic Order</li> <li>• Low reflectivity</li> <li>• Low resistivity</li> </ul>
		



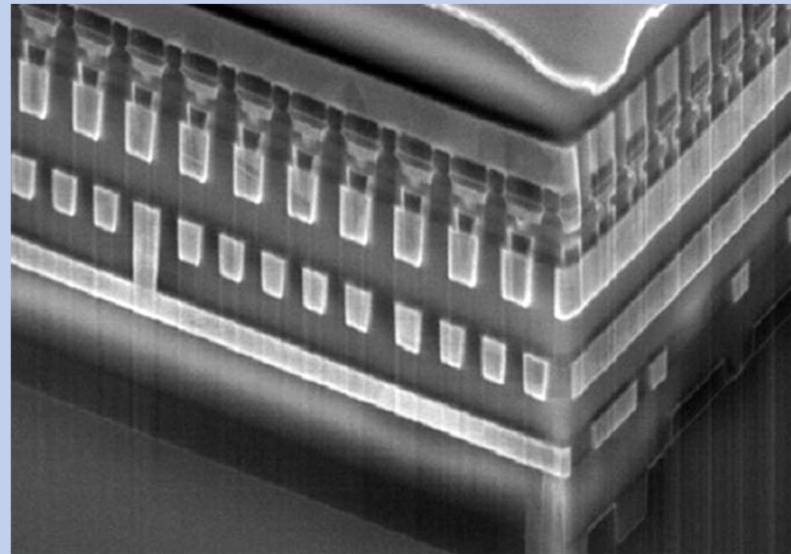
# Rewritable DVDs

- Uses optical lasers to change state of alloy
- Uses the change in its reflectivity to measure bits



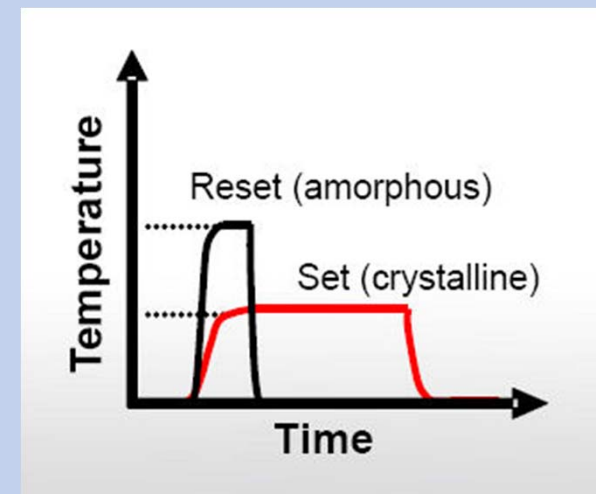
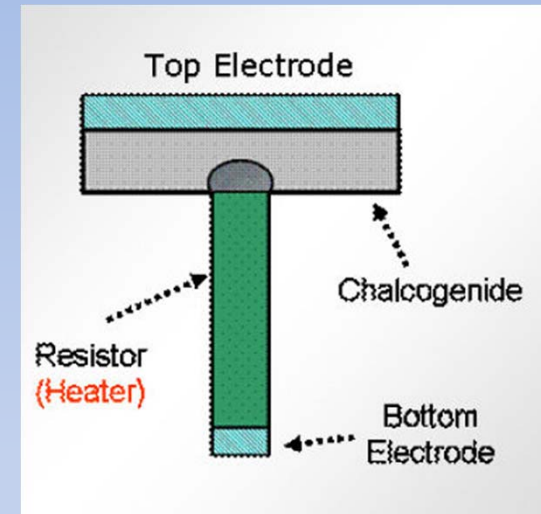
# Phase Change Memory

- May replace flash and RAM
- Uses small “heaters” to change the state of alloy
  - Different temperatures causes different states



# Write and Read

- Bit alterable
- Uses Joule heating(resistive heating)
  - Uses a intense voltage pulse to control heat
- Write time is limited by crystalline formation
- Read is simply measuring the resistance between two nodes
- Can be read like RAM
- Read and Write speeds improve with scaling



# Benefits

- Non-volatile memory
- Scalability (2 bits per cell)
- Better reliability
- Endurance (1 million write cycles)
- More resistance to radiation
- Less Power Consumption



# Barriers

- Needs a high current density
  - Write temperature is 600°C for GST
- Constant changes in state causes cell degradation
- Data retention based on room temperature
- More than twice as expensive as flash
- Heat leakage

# Future

- Carbon nanotubes instead of wires
  - Reduces power consumption 100x
- Outerspace applications
- Replace Flash and RAM memory in phones and computers
  - Most phones and computers use SRAM for fast read and write capabilities combined with Flash for non-volatile memory.

Questions?

# Resources

- [http://en.wikipedia.org/wiki/Phase-change\\_memory](http://en.wikipedia.org/wiki/Phase-change_memory)
- <http://agigatech.com/blog/pcm-phase-change-memory-basics-and-technology-advances/>
- [http://www.numonyx.com/Documents/WhitePapers/PCM\\_Basics\\_WP.pdf](http://www.numonyx.com/Documents/WhitePapers/PCM_Basics_WP.pdf)
- <http://www.enterprisestorageforum.com/technology/features/article.php/3862741/Phase-Change-Memory-The-Next-Big-Thing-in-Data-Storage.htm>
- <http://www.technologyreview.com/Infotech/20148/?a=f>
- <http://www.youtube.com/watch?v=EPsi1mBji2E&feature=related>